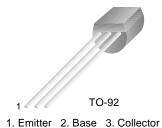


SS9015

Low Frequency, Low Noise Amplifier • Complement to SS9014



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|------------------|-----------------------------|-----------|-------|
| V_{CBO} | Collector-Base Voltage | -50 | V |
| V _{CEO} | Collector-Emitter Voltage | -45 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _C | Collector Current | -100 | Α |
| P _C | Collector Power Dissipation | 450 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|-------------------------------------|--|------|-------|-------|-------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_C = -100 \mu A, I_E = 0$ | -50 | | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_C = -1 \text{mA}, I_B = 0$ | -45 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = -100 \mu A, I_C = 0$ | -5 | | | V |
| I _{CBO} | Collector Cut-off Current | $V_{CB} = -50V, I_{E} = 0$ | | | -50 | nA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = -5V, I_{C} = 0$ | | | -50 | nA |
| h _{FE} | DC Current Gain | $V_{CE} = -5V, I_{C} = -1mA$ | 60 | 200 | 600 | , |
| V _{CE} (sat) | Collector-Base Saturation Voltage | $I_C = -100 \text{mA}, I_B = -5 \text{mA}$ | | -0.2 | -0.7 | , |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = -100 \text{mA}, I_B = -5 \text{mA}$ | | -0.82 | -1.0 | V |
| V _{BE} (on) | Base-Emitter On Voltage | $V_{CE} = -5V, I_{C} = -2mA$ | -0.6 | -0.65 | -0.75 | V |
| C _{ob} | Output Capacitance | $V_{CB} = -10V, I_{E} = 0$ f=1MHz | | 4.5 | 7.0 | pF |
| f _T | Current Gain Bandwidth Product | $V_{CE} = -5V, I_{C} = -10mA$ | 100 | 190 | | MHz |
| NF | Noise Figure | V_{CE} = -5V, I_{C} = -0.2mA f=1KHz, R_{S} =1K Ω | | 0.7 | 10 | dB |

h_{FE} Classification

| Classification | A | В | С |
|-----------------|----------|-----------|-----------|
| h _{FE} | 60 ~ 150 | 100 ~ 300 | 200 ~ 600 |

Typical Characteristics

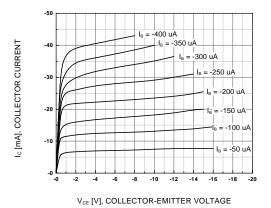


Figure 1. Static Characteristic

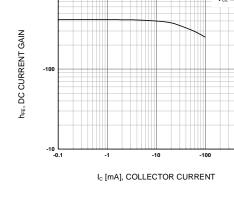


Figure 2. DC current Gain

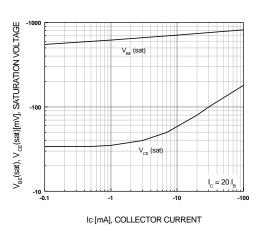


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

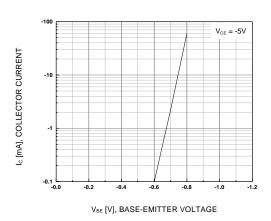


Figure 4. Base-Emitter On Voltage

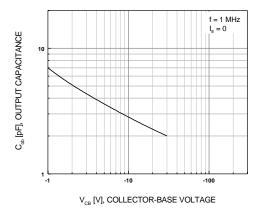


Figure 5. Collector Output Capacitance

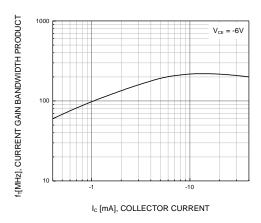
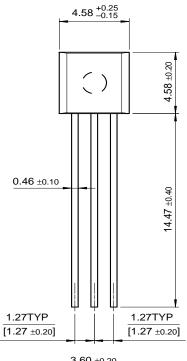


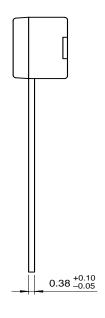
Figure 6. Current Gian Bandwidth Product

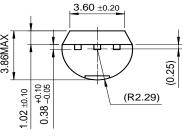
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Package Demensions

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